

wherein an uppermost layer of the insulating film is capable of preventing penetration of an alkaline metal.

32. A method according to claim 3, further comprising the step of:
forming an insulating film covering the plurality of TFTs,
wherein an uppermost layer of the insulating film is capable of preventing penetration of an alkaline metal.

33. A method according to claim 32, wherein the insulating film comprises:
an organic resin film;
an insulating layer being capable of preventing penetration of an alkaline metal on the organic resin film.

34. A method according to claim 32, wherein the insulating film comprising at least one of the elements selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and at least one of the elements selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus).

35. A method according to claim 32, wherein the insulating film comprises Si, Al, N, O and M, wherein M is at least an element selected from a rare-earth element, preferably an element selected from the group consisting of Ce (cesium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium), and Nd (neodymium)).--